

IN THE CLAIMS

Amend claim 16, cancel claim 17 without prejudice or disclaimer, and add new claims 18-24 as follows.

1-15. (Canceled).

16. (Currently Amended) A method for fabricating a hetero-junction bipolar transistor type semiconductor device, comprising the steps of:

(a) preparing a semiconductor substrate in which a collector layer, a base layer, and an emitter layer are formed sequentially;

(b) forming a first conductive layer on the main surface of said emitter layer;

(c) patterning said first conductive layer, thereby forming an emitter electrode and forming a dummy electrode so as to be separated from said emitter electrode;

(d) removing said emitter layer by using said emitter electrode and said dummy electrode as a mask, thereby exposing part of said base layer; and

(e) forming a second conductive layer serving as a base electrode on a part of said exposed base layer by using said emitter electrode and said dummy electrode as a mask.

17. (Canceled)

18. (New) A method for fabricating a hetero-junction bipolar transistor type semiconductor device according to Claim 16, wherein said base electrode is comprised of a first base electrode and a second base electrode;

said first and second base electrodes are separated by said dummy electrode; and

said second base electrode is formed closer to said emitter electrode than said first base electrode.

19. (New) A method for fabricating a hetero-junction bipolar transistor type semiconductor device according to Claim 18, wherein

said hetero-junction bipolar transistor type semiconductor device has a plurality of said base layers and emitter layers;

said base layers are separated from each other;
said emitter layers are separated from each other; and
said first and second base electrodes are formed on each
of said base layers.

20. (New) A method for fabricating a hetero-junction bipolar transistor type semiconductor device according to Claim 19, wherein a common base wiring for electrically connecting said first base electrodes is formed.

21. (New) A method for fabricating a hetero-junction bipolar transistor type semiconductor device according to Claim 18, further comprising the step of:

(f) between said steps (d) and (e), forming said second conductive layer over said emitter electrode, said dummy electrode, and said exposed base layer.

22. (New) A method for fabricating a hetero-junction bipolar transistor type semiconductor device according to Claim 18, wherein said base layer between said first and second base electrodes functions as a base resistor.

23. (New) A method for fabricating a hetero-junction bipolar transistor type semiconductor device according to Claim 18, wherein said emitter electrode and said dummy electrode are comprised of a same material.

24. (New) A method for fabricating a hetero-junction bipolar transistor type semiconductor device according to Claim 18, wherein said collector layer and base layer are comprised of GaAs; and said emitter layer is comprised of InGaP.